

ABSTRACT OF THE DISCLOSURE

5 A method according to the present invention for
fabricating high light extraction photonic devices
comprising growing an epitaxial semiconductor structure
on a substrate and depositing a first mirror layer on the
epitaxial semiconductor structure such that the epitaxial
10 semiconductor structure is sandwiched between the first
mirror layer and the substrate. Flip-chip mounting the
epitaxial semiconductor structure, with its first mirror
and substrate on a submount such that the epitaxial
15 semiconductor device structure is sandwiched between the
submount and substrate. The substrate is then removed
from the epitaxial structure by introducing an etch
environment to the substrate. A second mirror layer is
deposited on the epitaxial semiconductor structure such
20 that the epitaxial semiconductor structure is sandwiched
between the first and second mirror layers. A device
according to the present invention comprising a resonant
cavity light emitting diode (RCLED) mounted to a
submount.